

PSMN4R6-60BS

N-channel 60 V, 4.4 mΩ standard level MOSFET in D2PAK Rev. 1 — 22 March 2012 Product data of

Product data sheet

1. **Product profile**

1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I_D	drain current	T _{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	-	100	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	211	W
T _j	junction temperature			-55	-	175	°C
Static chara	ncteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 100 \text{ °C}; \text{see}$ Figure 12; see Figure 13		-	5.98	7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 13		-	3.74	4.4	mΩ
Dynamic ch	naracteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 30 \text{ V};$		-	14.8	-	nC
Q _{G(tot)}	total gate charge	see <u>Figure 14</u> ; see <u>Figure 15</u>		-	70.8	-	nC
Avalanche i	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω ; unclamped		-	-	266	mJ

^[1] Continuous current is limited by package.



2. Pinning information

Table 2. Pinning information

		,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

^[1] It is not possible to make connection to pin 2

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN4R6-60BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
PSMN4R6-60BS	PSMN4R6-60BS

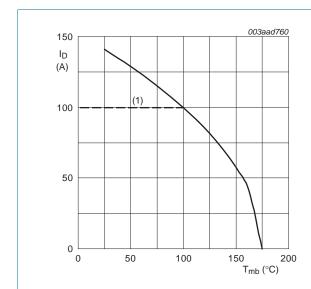
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		•				
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I_D	drain current	T _{mb} = 100 °C; see <u>Figure 1</u>	<u>[1]</u>	-	99.7	Α
		T _{mb} = 25 °C; see <u>Figure 1</u>	<u>[1]</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p = 10 \mu s$; $T_{mb} = 25 \text{ °C}$; see Figure 3		-	565	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	211	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-dra	ain diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	100	Α
I _{SM}	peak source current	pulsed; $t_p = 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	565	Α
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; V_{sup} ≤ 60 V; R_{GS} = 50 Ω ; unclamped		-	266	mJ

[1] Continuous current is limited by package.



 $V_{\rm GS} \ge$ 10 V; (1) capped at 100 A due to package.

Fig 1. Continuous drain current as a function of mounting base temperature

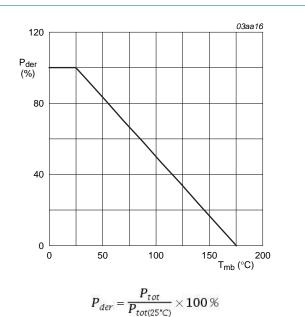


Fig 2. Normalized total power dissipation as a

function of mounting base temperature

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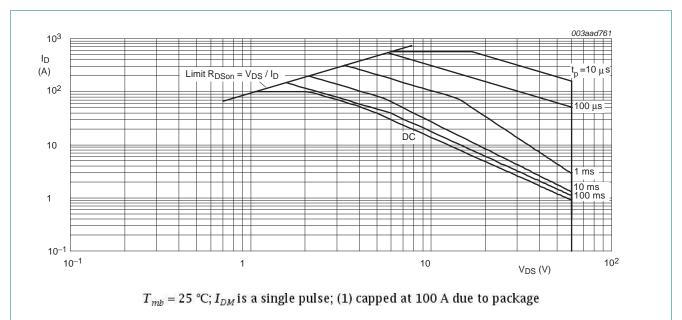


Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.38	0.71	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint; mounted on a printed circuit board	-	50	-	K/W

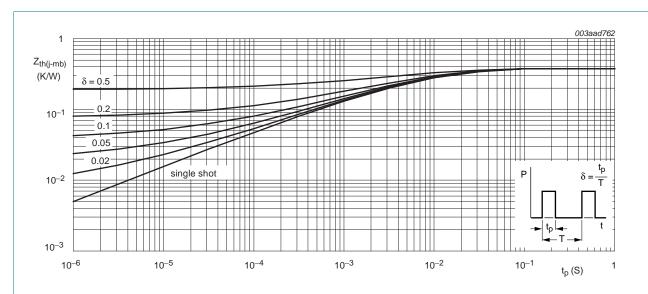


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25 \text{ °C}$; see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
V_{GSth}	V _{GSth} gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 11	-	-	4.8	V
		$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 11	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 125 °C	-	-	200	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	10	100	nΑ
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	10	100	nΑ
R _{DSon} drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see Figure 12; see Figure 13	-	8.6	10.1	mΩ	
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see Figure 12; see Figure 13	-	5.98	7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13	-	3.74	4.4	mΩ
R _G	gate resistance	f = 1 MHz	-	0.79	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	63	-	nC
		I _D = 25 A; V _{DS} = 30 V; V _{GS} = 10 V;	-	70.8	-	nC
Q _{GS}	gate-source charge	see Figure 14; see Figure 15	-	19.5	-	nC
Q _{GS(th)}	pre-threshold gate-source charge		-	13.5	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	6	-	nC
Q _{GD}	gate-drain charge		-	14.8	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}$; $V_{DS} = 30 \text{ V}$; see Figure 14; see Figure 15	-	4.3	-	V
C _{iss}	input capacitance	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	4426	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	567	-	pF
C _{rss}	reverse transfer capacitance		-	293	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	26	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$	-	24	-	ns
t _{d(off)}	turn-off delay time		-	58	-	ns
t _f	fall time		-	22	-	ns

Table 7. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 17	-	0.81	1.1	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = -100 \text{ A/}\mu\text{s}$;	-	45	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}$	-	64	-	nC

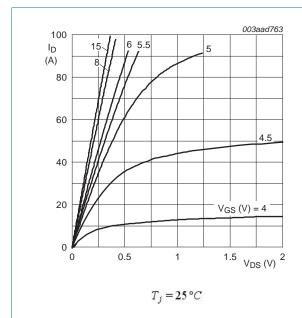


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

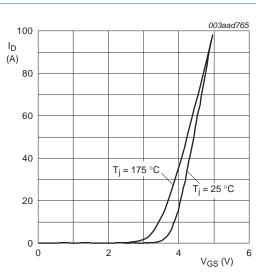
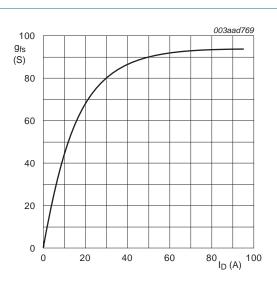


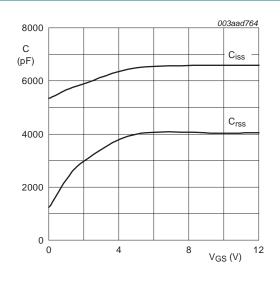
Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

 $V_{DS} > I_D \times R_{DSon}$



 $T_j = 25$ °C; $V_{DS} = 10 \text{ V}$

Fig 6. Forward transconductance as a function of drain current; typical values



 $f = 1 \text{ MHz}; V_{DS} = 0 \text{ V}$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

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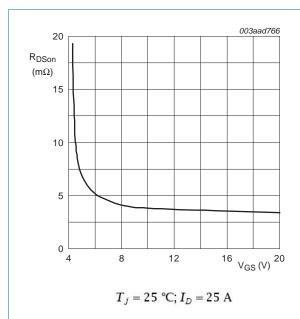
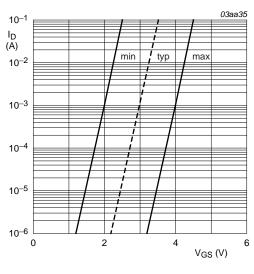


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



 $T_j = 25 \,^{\circ}C; V_{DS} = 5V$

Fig 10. Sub-threshold drain current as a function of gate-source voltage

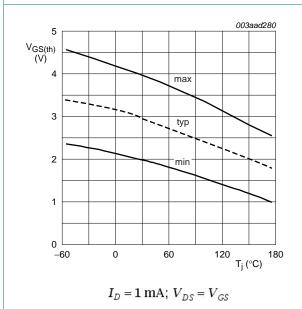


Fig 11. Gate-source threshold voltage as a function of junction temperature

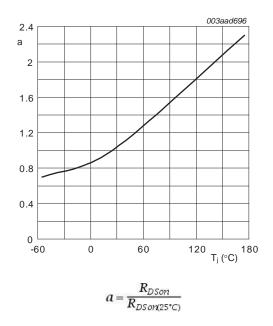
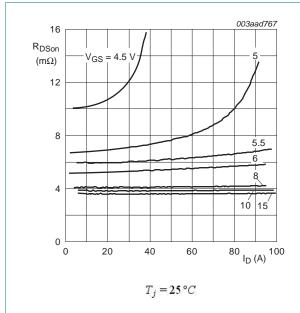


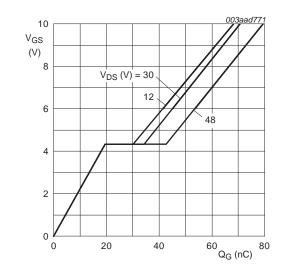
Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature.

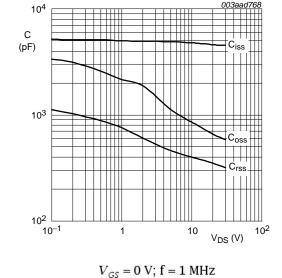


V_{GS}(pl)
V_{GS}(th)
V_{GS}
Q_{GS1} Q_{GS2}
Q_G(tot)
003aaa508

Fig 13. Drain-source on-state resistance as a function of drain current; typical values

Fig 14. Gate charge waveform definitions

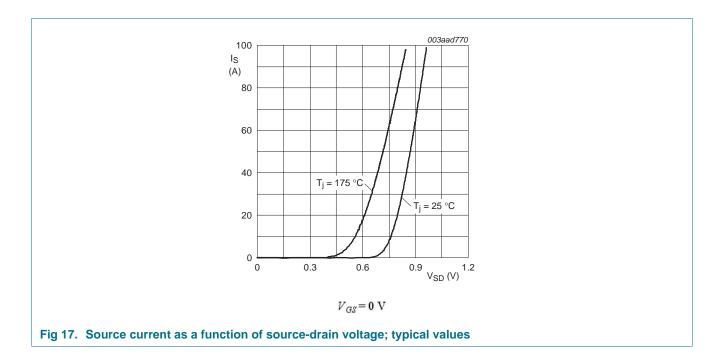




 $T_j = 25$ °C; $I_D = 25$ A

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

Fig 15. Gate-source voltage as a function of gate charge; typical values



8. Package outline

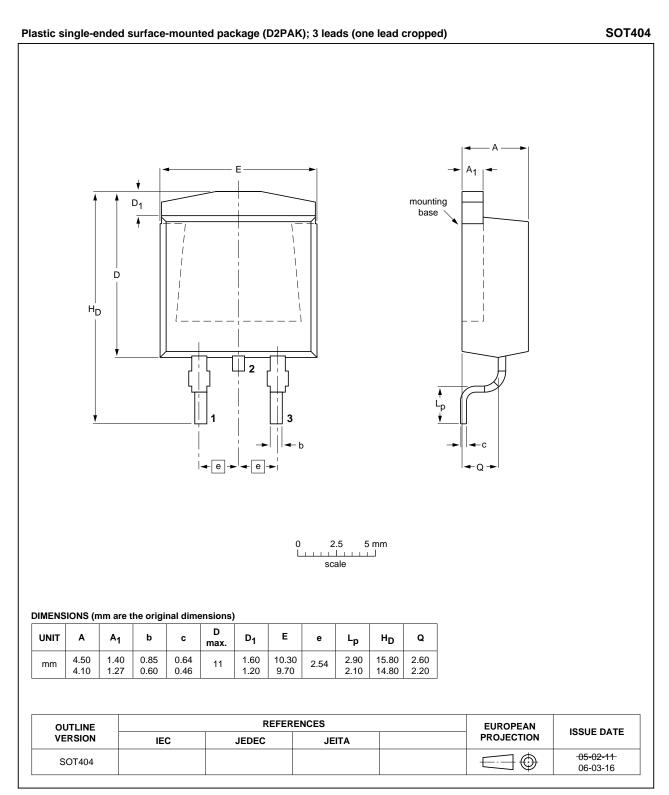


Fig 18. Package outline SOT404 (D2PAK)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN4R6-60BS v.1	20120322	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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